大连理工大学
DALIAN UNIVERSITY OF TECHNOLOGY

实验进展

徐瑞良

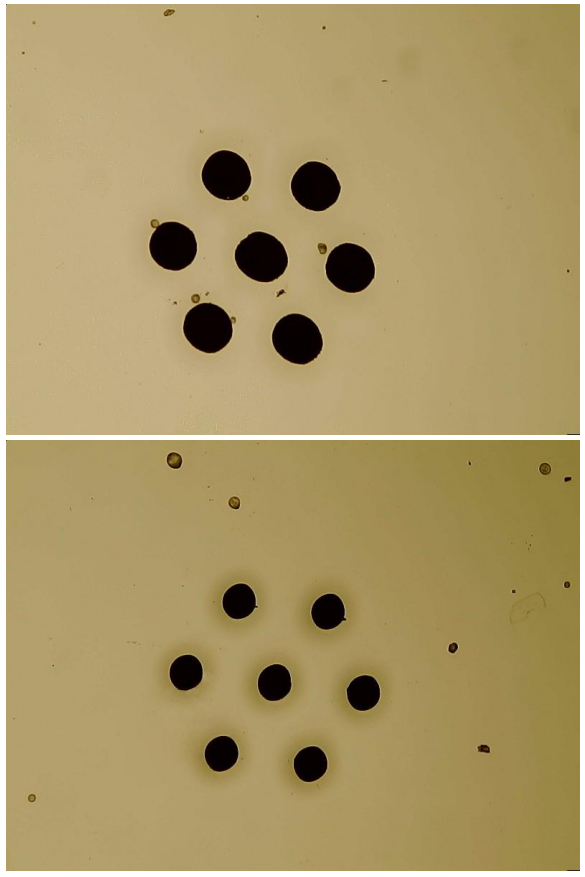
大连理工大学国家示范性微电子学院（筹）

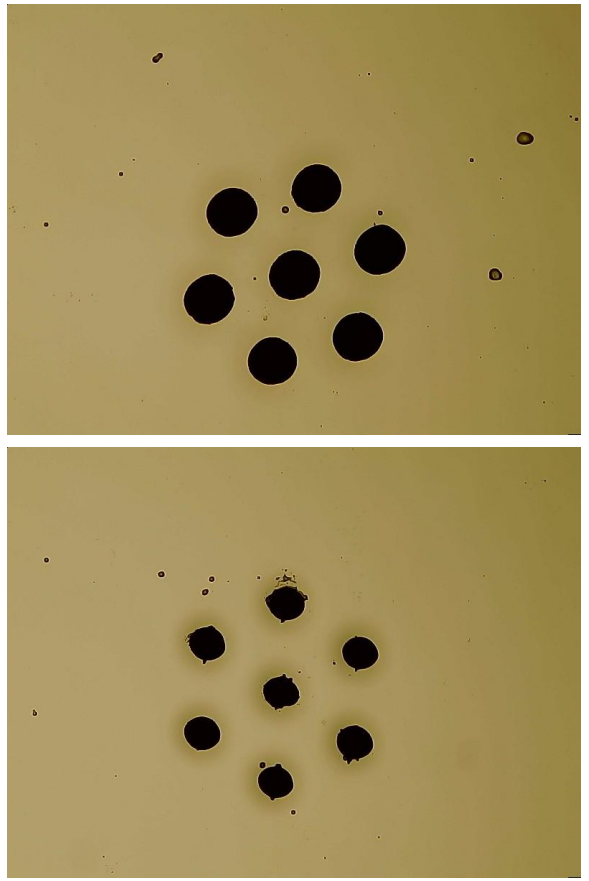
2021年9月28日

After chemical cleaning（diameter： 100um; distance： 100um）

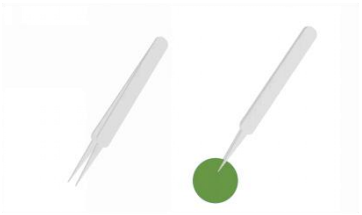
Incident surface

Exit surface

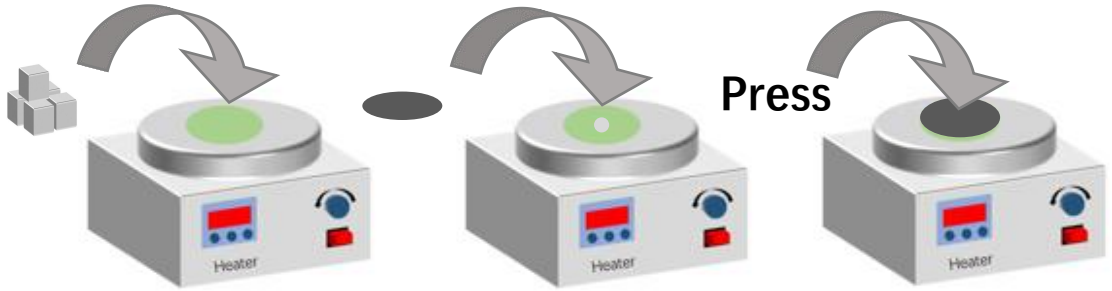


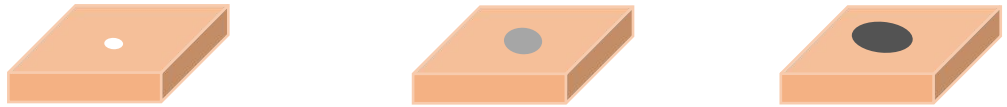


Design	Sample 1（um）	Sample 2（um）
Incident Diameter	103	104
Exit Diameter	81	83



Diameter：100um



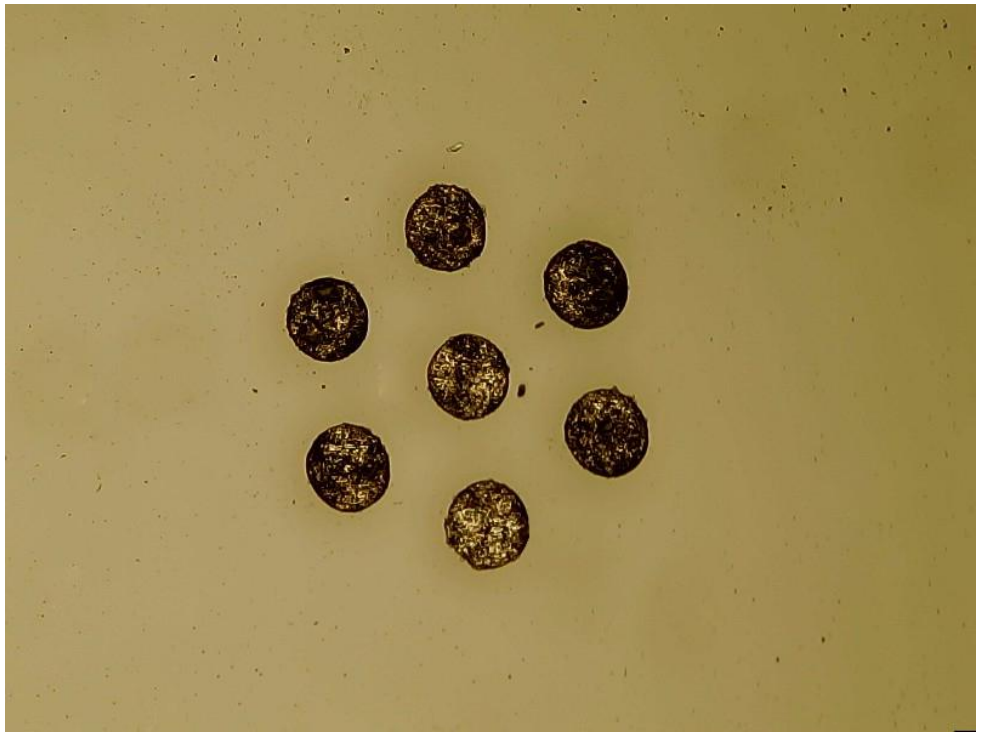




SiC Substrate

Indium

Silicon wafer

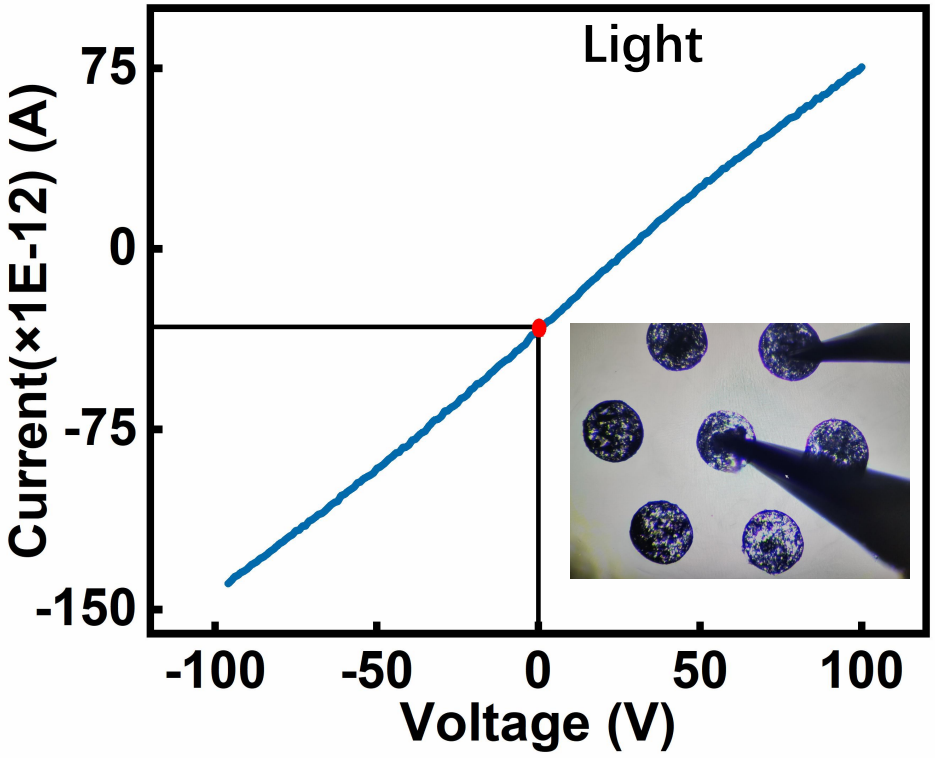


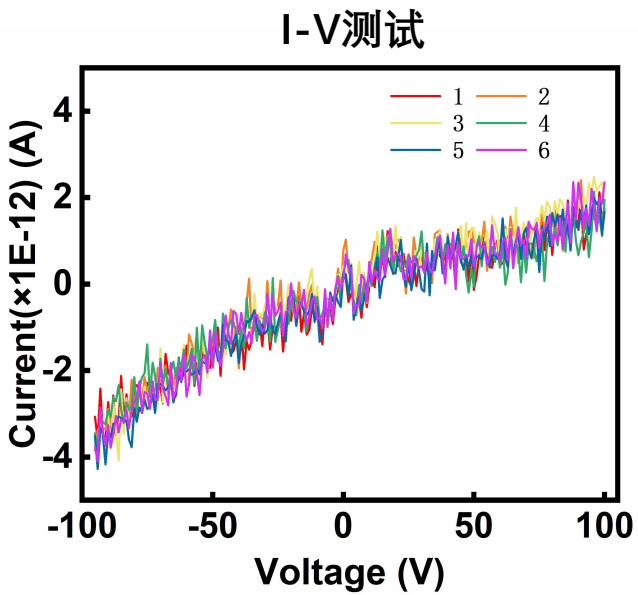
Incident Surface -100um



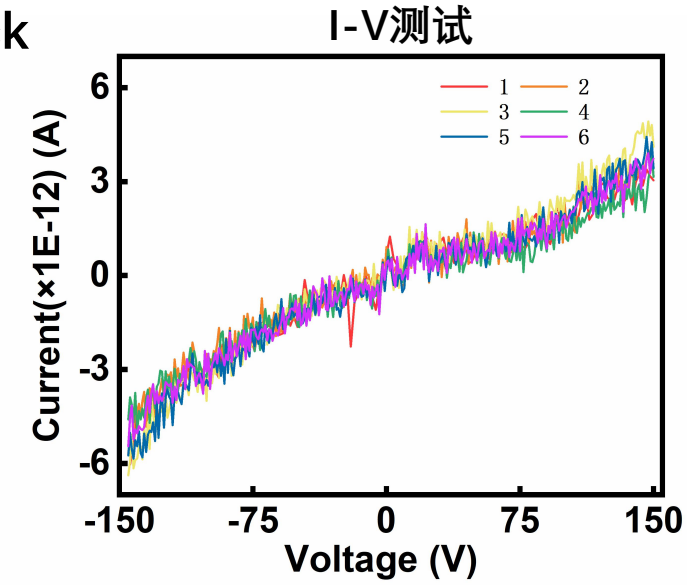
Exit Surface -100um

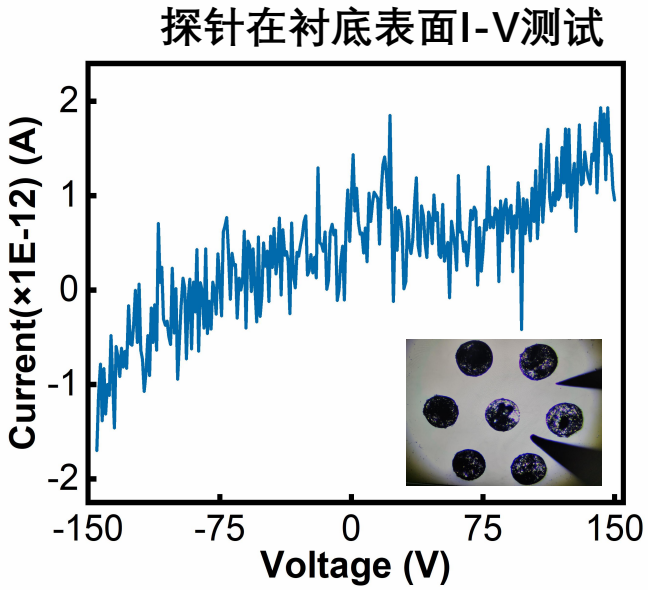
Test

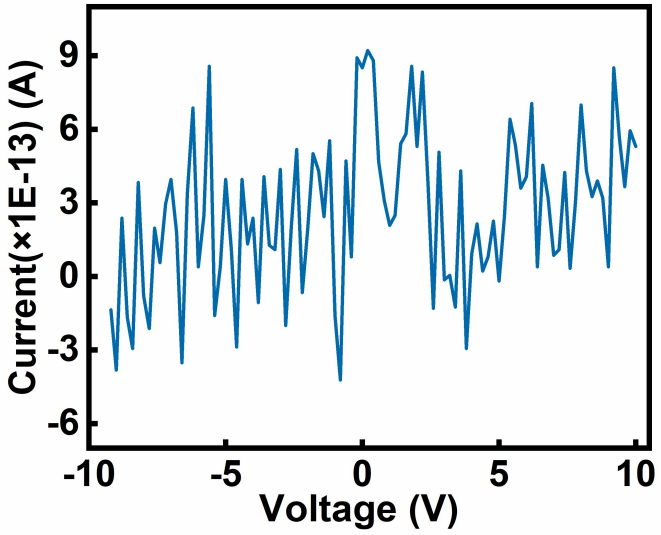

Light
Current(×1E-12) (A)
75
0
-75
-150
-100
-50
0
50
100
Voltage (V)


I-V测试
Current(×1E-12) (A)
4
2
0
-2
-4
1
2
3
4
5
6
-100
-50
0
50
100
Voltage (V)

Black


I-V测试
Current(×1E-12) (A)
6
3
0
-3
-6
1
2
3
4
5
6
-150
-75
0
75
150
Voltage (V)


探针在衬底表面I-V测试
Current(×1E-12) (A)
2
1
0
-1
-2
-150
-75
0
75
150
Voltage (V)


空测
Current(×1E-13) (A)
9
6
3
0
-3
-6
-10
-5
0
5
10
Voltage (V)

宽带隙半导体

谢谢大家

欢迎提出宝贵意见